

Notice of References Cited	Application/Control No. 10/688,954		Applicant(s)/Patent Under Reexamination KIM ET AL.	
	Examiner W. David Coleman		Art Unit 2823	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,980,720	11-1999	Park et al.	205/118
	B	US-2001/0016420	08-2001	Chou, Ming-Chun	438/687
	C	US-6,773,573	08-2004	Gabe et al.	205/296
	D	US-4,399,020	08-1983	Branchick et al.	204/269
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	Shin et al. "Influence of Cu-decoration to Individual Crystal Originated Pits on Si Wafer", Japanese Journal of Applied Physics, vol. 42, pp. 4187-4192, July 2003				
	V	Itsumi et al., "Gate Oxide Defects in MOSLISs and Octahedral Void Defects in Czochralski Silicon" Japanes Journal of Applied Physics, vol. 37, pp 1228-1235, March 1998				
	W	Park et al., "Nature of Surface and Bulk Defect Induced by Low Dose Oxygeng Implantation in Separation by Implanted Oxygen Wafers", Japanese Journal of Applied Physics, vol., 40, pp. 2178-2185, April 2001				
	X					

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.